

December 2007

# FPAB30BH60

# Smart Power Module(SPM®) for Front-End Rectifier

### **General Description**

FPAB30BH60 is an advanced smart power module(SPM®) of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is futher enhanced by the integrated under-voltage lock-out and over-current protection function.

### **Features**

- Low thermal resistance due to AjO<sub>3</sub>-DBC substrate
- 600V-30A 1-phase IGBT PWM semi-converter including a drive IC for gate driving and protection
- Typical switching frequency of 20kHz
- · Isolation rating of 2500Vrms/min.

### **Applications**

• AC 85V ~ 264V single-phase front-end rectifier

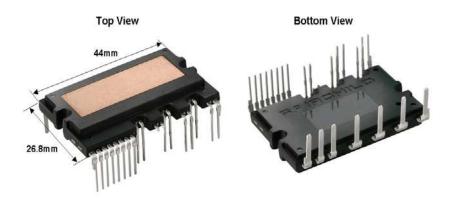


Fig. 1.

# **Integrated Power Functions**

• PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

# **Integrated Drive, Protection and System Control Functions**

- For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) potection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

# **Pin Configuration**

### **Top View**

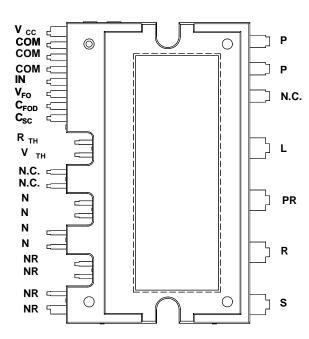


Fig. 2.

# **Pin Descriptions**

Pin Number	Pin Name	Pin Description
1	V <sub>CC</sub>	Common Bias Voltage for IC and IGBTs Driving
2,3,4	COM	Common Supply Ground
5	IN <sub>(R)</sub>	Signal Input for Low-side R-phase IGBT
6	V <sub>FO</sub>	Fault Output
7	C <sub>FOD</sub>	Capacitor for Fault Output Duration Time Selection
8	C <sub>SC</sub>	Capacitor (Low-pass Filter) for Over Current Detection
9	R <sub>(TH)</sub>	NTC Thermistor terminal
10	V <sub>(TH)</sub>	NTC Thermistor terminal
11,12	N.C	No Connection
13~16	N	IGBT emitter
17~20	N <sub>R</sub>	Negative DC-Link of Rectifier
21,22	Р	Positive Rail of DC-Link
23	N.C	No Connection
24	L	Reactor connection pin
25	$P_{R}$	Positive DC–Link of Rectifier
26	R	AC input for R-phase
27	S	AC input for S-phase

<sup>\* 11</sup>th and 12th pins are cut. Please refer to package outline drawings for more detail.

# **Internal Equivalent Circuit and Input/Output Pins**

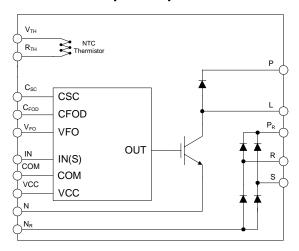


Fig. 3.

# **Package Marking & Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FPAB30BH60	FPAB30BH60	SPM27-IA	-	-	10

# **Absolute Maximum Ratings** ( $T_J = 25$ °C, Unless Otherwise Specified)

### **Converter Part**

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V <sub>i</sub>	Applied between R-S	264	$V_{RMS}$
Supply Voltage (Surge)	V <sub>i(Surge)</sub>	Applied between R-S	500	V
Output Voltage	$V_{PN}$	Applied between P- N	450	V
Output Voltage (Surge)	V <sub>PN(Surge)</sub>	Applied between P- N	500	V
Collector-emitter Voltage	V <sub>CES</sub>		600	V
Input Current (100% Load)	l <sub>i</sub>	$T_C < 95^{\circ}C$ , $V_i=220V$ , $V_{PN}=390V$ , $V_{PWM}=20kHz$	25	Α
Input Current (125% Load)	I <sub>i(125%)</sub>	$T_C$ < 95°C, V <sub>i</sub> =220V, $V_{PN}$ = 390V, $V_{PWM}$ =20kHz, 1min Non-repetitive	30	А
Collector Dissipation	P <sub>C</sub>	T <sub>C</sub> = 25℃ per One IGBT	169	W
Operating Junction Temperature	TJ	(Note 1)	-20 ~ 150	C

### **Control Part**

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	$V_{CC}$	Applied between V <sub>CC</sub> - COM	20	V
Input Signal Voltage	V <sub>IN</sub>	Applied between IN - COM	-0.3~5.5	V
Fault Output Supply Voltage	$V_{FO}$	Applied between V <sub>FO</sub> - COM	-0.3~V <sub>CC</sub> +0.3	V
Fault Output Current	I <sub>FO</sub>	Sink Current at V <sub>FO</sub> Pin	5	mA
Current Sensing Input Voltage	V <sub>SC</sub>	Applied between C <sub>SC</sub> - COM	-0.3~V <sub>CC</sub> +0.3	V

### **Total System**

Item	Symbol	Condition	Rating	Unit
Module Case Operation Temperature	T <sub>C</sub>		-20 ~ 100	C
Storage Temperature	T <sub>STG</sub>		-40 ~ 125	C
Isolation Voltage	V <sub>ISO</sub>	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V <sub>rms</sub>

### **Thermal Resistance**

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to Case Thermal	$R_{\theta(j-c)Q}$	IGBT	-	-	0.74	€/M
Resistance	$R_{\theta(j-c)F}$	FRD	-	-	1.44	€\M
(Referenced to PKG center)	$R_{\theta(j-c)R}$	Rectifier	•	-	2.07	€\M

2. For the measurement point of case temperature( $T_{\mbox{\scriptsize C}}$ ), please refer to Fig. 2.

Note 1. The maximum junction temperature rating of the power chips integrated within the SPM® is 150 °C(@T<sub>C</sub>  $\leq$  100°C). However, to insure safe operation of the SPM®, the average junction temperature should be limited to T<sub>J(ave)</sub>  $\leq$  125°C (@T<sub>C</sub>  $\leq$  100°C)

# **Electrical Characteristics** ( $T_J = 25$ $^{\circ}$ C, Unless Otherwise Specified)

### **Converter Part**

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
IGBT saturation voltage	V <sub>CE(sat)</sub>	V <sub>CC</sub> =15V, V <sub>IN</sub> = 5V; I <sub>C</sub> =30A	-	2.0	2.8	V
FRD forward voltage	V <sub>FF</sub>	I <sub>F</sub> = 30A	-	1.8	2.5	V
Rectifier forward voltage	$V_{FR}$	I <sub>F</sub> = 30A	-	1.2	1.5	V
Peak surge current	I <sub>FSM</sub>	Non-repetitive, 60Hz single half-sine wave	200	-	-	Α
Switching Times	t <sub>ON</sub>	$V_{PN} = 400V, V_{CC} = 15V, I_{C} = 30A$	-	650	-	ns
	t <sub>C(ON)</sub>	V <sub>IN</sub> = 0V ↔ 5V, Inductive Load	-	400	-	ns
	t <sub>OFF</sub>	(Note 3)	-	620	-	ns
	t <sub>C(OFF)</sub>	(10000)	-	200	-	ns
	t <sub>rr</sub>		-	60	-	ns
	I <sub>rr</sub>		-	3.5	-	Α
Collector - emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub>	-	-	250	μА

### **Control Part**

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Quiescent V <sub>CC</sub> Supply Current	I <sub>QCCL</sub>	$V_{CC} = 15V$ , $IN = 0V$ $V_{CC} - COM$	-	-	26	mA
Fault Output Voltage	$V_{FOH}$	$V_{SC}$ = 0V, $V_{FO}$ Circuit: 4.7k $\Omega$ to 5V Pull-up	4.5	-	-	V
	V <sub>FOL</sub>	$V_{SC}$ = 1V, $V_{FO}$ Circuit: 4.7k $\Omega$ to 5V Pull-up	-	-	0.8	V
Over Current Trip Level	V <sub>SC(ref)</sub>	V <sub>CC</sub> = 15V	0.45	0.5	0.55	V
Supply Circuit Under-	UV <sub>CCD</sub>	Detection Level	10.7	11.9	13.0	V
Voltage Protection	UV <sub>CCR</sub>	Reset Level	11.2	12.4	13.2	V
Fault-out Pulse Width	t <sub>FOD</sub>	C <sub>FOD</sub> = 33nF (Note 4)	1.4	1.8	2.0	ms
ON Threshold Voltage	V <sub>IN(ON)</sub>	Applied between IN - COM	3.0	-	-	V
OFF Threshold Voltage	V <sub>IN(OFF)</sub>		-	-	0.8	V
Resistance of Thermistor	R <sub>TH</sub>	@ T <sub>C</sub> = 25℃ (Note Fig. 9)	-	50	-	kΩ
		@ T <sub>C</sub> = 100℃ (Note Fig. 9)	-	2.99	-	kΩ

<sup>3. 1&</sup>lt;sub>ON</sub> and t<sub>OFF</sub> include the propagation delay time of the internal drive IC. t<sub>C(ON)</sub> and t<sub>C(OFF)</sub> are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

Note 4. The fault-out pulse width  $t_{FOD}$  depends on the capacitance value of  $C_{FOD}$  according to the following approximate equation :  $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$ 

# **Electrical Characteristics**

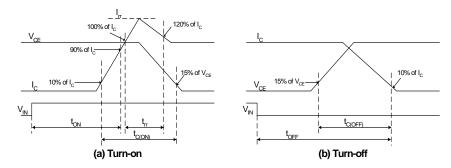


Fig. 4. Switching Time Definition

# **Mechanical Characteristics and Ratings**

Item	Condition			Limits		
item	C	Condition			Max.	Units
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N• m	0.51	0.62	0.72	N• m
Device Flatness	Note Fig. 5		0	-	+120	μ <b>m</b>
Weight				15.00	-	g

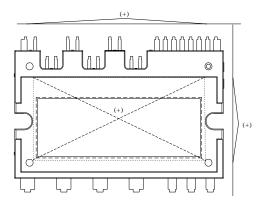
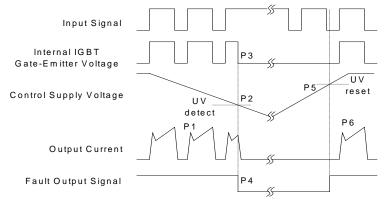


Fig. 5. Flatness Measurement Position

### **Time Charts of SPMs Protective Function**

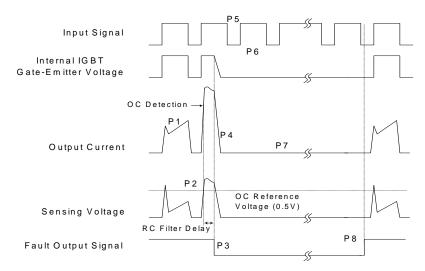


P1: Normal operation - IGBT ON and conducting current

P2 : Under voltage detection P3 : IGBT gate interrupt P4 : Fault signal generation P5 : Under voltage reset

P6: Normal operation - IGBT ON and conducting current

Fig. 6. Under-Voltage Protection



P1: Normal operation - IGBT ON and conducting current

P2 : Over current detection

P3: IGBT gate interrupt / Fault signal generation

P4 : IGBT is slowly turned off

P5 : IGBT OFF signal

P6: IGBT ON signal - but IGBT cannot be turned on during the fault Output activation

P7: IGBT OFF state

P8: Fault Output reset and normal operation start

Fig. 7. Over Current Protection

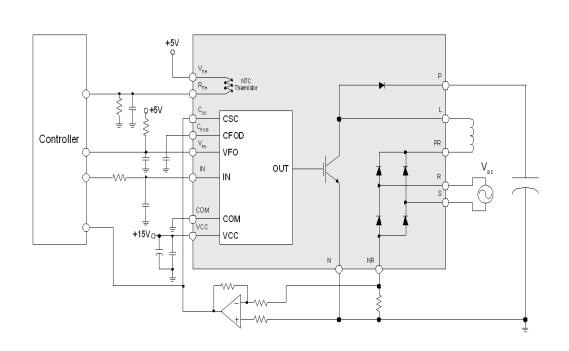


Fig. 8. Application Example
R-T Graph

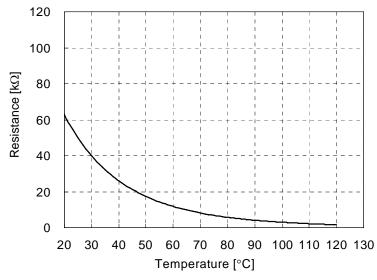
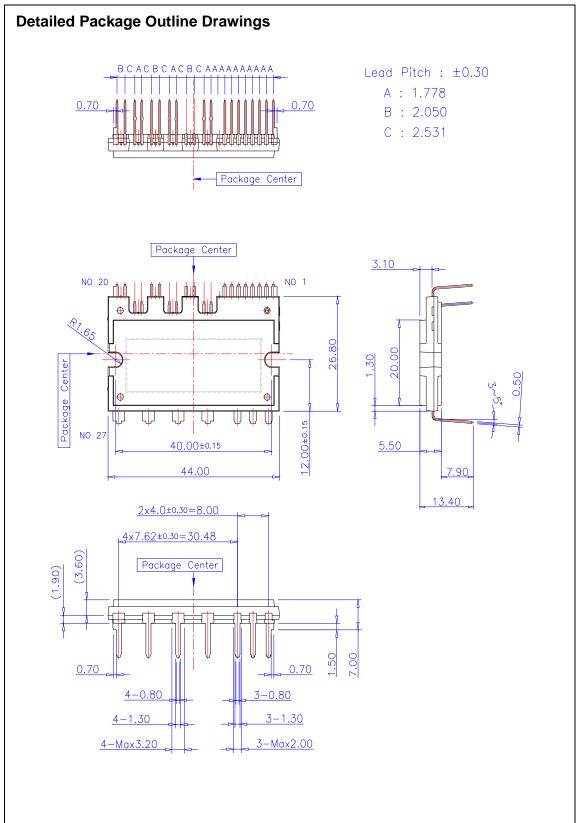
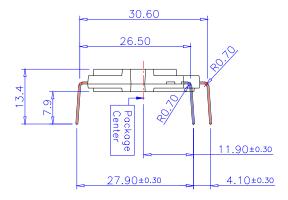


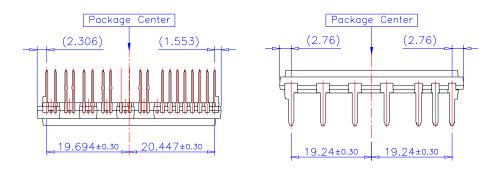
Fig. 9. R-T Curve of the Built-in Thermistor



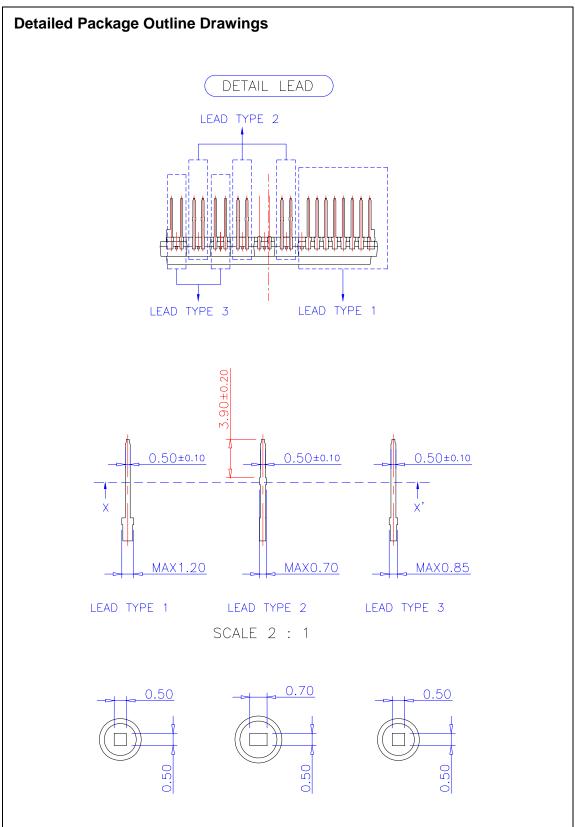
# **Detailed Package Outline Drawings**



Lead Forming Dimension



PKG Center to Lead Distance



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